

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Chen, *et al.* Attorney Docket: TSM6283131RI
Serial No. TBD Filed: Herewith
Reissue of: 6,283,131 B1 Issued: September 4, 2001
Title: IN-SITU STRIP PROCESS FOR POLYSILICON ETCHING IN DEEP SUB-MICRON TECHNOLOGY

Mail Stop Reissue
Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

**DECLARATION AND POWER OF ATTORNEY FOR APPLICATION
FOR REISSUE OF U.S. PATENT NO. 6,283,131**

Dear Sir:

As a below-named inventor, I hereby declare that:

Pursuant to the requirements of 37 C.F.R. §1.63(a)(3), my residence and country of citizenship are provided below next to my name.

I hereby state that I am the original, first and joint inventor of the subject matter which is described and claimed in U.S. Patent 6,283,131, and of the subject matter which is claimed in the claims in the application for reissue of U.S. Patent 6,283,131, which application is attached hereto.

I hereby state that I have reviewed and understand the contents of the specification, including the claims, as included with this application for reissue.

Pursuant to the requirements of 37 C.F.R. §1.175(a)(1), I believe that U.S. Patent No. 6,283,131 is wholly or partly inoperative by reason of claiming less than I had a right to claim in the patent.

At Least One Error under 35 U.S.C. §251 as to the Scope of the Original Claims being Relied on as the Basis for Reissue.

The error involves the failure to claim the invention as broadly as I am entitled. One error upon which reissue is based is the unnecessary limitation in claim 16 of "providing a polysilicon layer." The limitation to a conductive layer being fabricated from polysilicon is not necessary to my invention or to distinguish over the prior art. This error can be corrected by removal of the unnecessary limitation "polysilicon" as per the accompanying amendment to the claims. Other errors are sought to be corrected as well.

Pursuant to requirements of 37 C.F.R. §1.175(a)(2), I state that all errors being corrected in the reissue application up to the time of filing this Declaration arose without any deceptive intention on the part of the Applicant.

Pursuant to requirements of 37 C.F.R. §1.63(b)(3), I acknowledge the duty to disclose to the Office all information known to Applicant to be material to patentability as defined in 37 C.F.R. §1.56.

Pursuant to requirements of 37 C.F.R. §1.68, I declare further that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

I hereby appoint the following individuals as my representatives with full power of substitution and revocation to prosecute a Reissue application upon U.S. Patent No. 6,283,131

and to transact all business in the United States Patent and Trademark Office connected therewith:

Steven H. Slater, Reg. No. 35,361

Ira S. Matsil, Reg. No. 35,272

Brian A. Carlson, Reg. No. 37,793

James C. Kesterson, Reg. No. 25,882

Kay Houston, Reg. No. 38,495

Barry W. Dove, Reg. No. 45,862

Roger C. Knapp, Reg. No. 46,836

Full name of first inventor: Horng-Wen Chen

Inventor's Signature: _____

Date: _____

Residence:

Citizenship:

Post Office Address:

Full name of second inventor: Chi-How Wu

Inventor's Signature: _____

Date: _____

Residence:

Citizenship:

Post Office Address:

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Chen, *et al.* Attorney Docket: TSM6283131RI
Serial No. TBD Filed: Herewith
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ASSENT TO APPLICATION FOR REISSUE OF U.S. PATENT NO. 6,283,131
AND OFFER TO SURRENDER U.S. PATENT NO. 6,283,131

Pursuant to 37 C.F.R. §1.172, Taiwan Semiconductor Manufacturing Company, Ltd., as assignee of the entire right, title and interest in and to U.S. Patent No. 6,283,131, entitled IN-SITU STRIP PROCESS FOR POLYSILICON ETCHING IN DEEP SUB-MICRON TECHNOLOGY, hereby assents to the Application for Reissue of U.S. Patent No. 6,283,131, issued September 4, 2001.

Pursuant to 37 C.F.R. §1.178, assignee, Taiwan Semiconductor Manufacturing Company, Ltd., hereby offers to surrender U.S. Patent No. 6,283,131 upon notification of the allowability of said Application for Reissue.

A certificate under 37 C.F.R. §3.73(b) is attached.

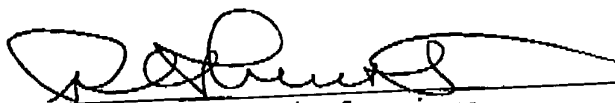
I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001 and that such willful false

TSM6283131RI

statements may jeopardize the validity of the application, any patent issued thereon, or any patent to which this declaration is directed.

I am authorized to act on behalf of the assignee.

Name of Assignee: Taiwan Semiconductor Manufacturing Company, Ltd.



Signature of person signing for assignee

8-27-03
Date

RICHARD L. THURSTON

Vice President and General Counsel
Printed name and title of person signing for assignee

Please type a plus sign (=) inside this box → ☐

PTO/SB/81 (02-01)

Approved for use through 10/31/2002. OMB 0651-0035

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**POWER OF ATTORNEY OR
AUTHORIZATION OF AGENT**

Application Number	Reissue of 6,283,131
Filing Date	Herewith
First Named Inventor	Chen, et al.
Title	In-SITU Strip Process for Polysilicon Etching in Deep Sub-Micron Technology
Group Art Unit	TBD
Examiner Name	TBD
Attorney Docket Number	TSM6283131RI

I hereby appoint:

☒ Practitioners at Customer Number

25962 →

OR

☐ Practitioner(s) named below:

Name	Registration Number

as my/our attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.

Please change the correspondence address for the above-identified application to:

☐ The above-mentioned Customer Number.

OR

☐ Practitioners at Customer Number

OR

☒ Firm or
Individual Name

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Zip 75262-5793

Country USA

Telephone 972-732-1001

Fax 972-732-9218

I am the:

☐ Applicant/Inventor☒ Assignee of record of the entire interest. See 37 CFR 3.71.

Statement under 37 CFR 3.73(b) is enclosed. (Form PTO/SB/96).

SIGNATURE of Applicant or Assignee of Record

Name

RICHARD L. THURSTON

Signature

Date

8-27-03

NOTE: Signatures of all the inventors or assignees of record of the entire interest or their representative(s) are required. Submit multiple forms if more than one signature is required, see below.

☒ *Total of 1 form is submitted.

Burden Hour Statement: This form is estimated to take 3 minutes to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.

PTO/SB/98 (08-00)

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STATEMENT UNDER 37 CFR 3.73(b)

Applicant/Patent Owner: Chen, et al.

Application No./Patent No.: 6,283,131 B1 Filed/Issued Date: September 4, 2001

Entitled: In-SITU Strip Process for Polysilicon Etching In Deep Sub-Micron Technology

Taiwan Semiconductor Manufacturing Company, Ltd., a corporation

(Name of Assignee)

(Type of Assignee, e.g., corporation, partnership, university, government agency, etc.)

states that it is:

1. ☒ the assignee of the entire right, title, and interest; or
2. ☐ an assignee of less than the entire right, title and interest.
The extent (by, percentage) of its ownership interest is _____ %

in the patent application/patent identified above by virtue of either:

- A. ☒ An assignment from the inventor(s) of the patent application/patent identified above. The assignment was recorded in the United States Patent and Trademark Office at Reel/Frame 011182/0578, or for which a copy thereof is attached.

OR

- B. ☐ A chain of title from the inventor(s), of the patent application/patent identified above, to the current assignee as shown below:

1. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.
2. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.
3. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.

☐ Additional documents in the chain of title are listed on a supplemental sheet.

- ☐ Copies of assignments or other documents in the chain of title are attached.

[NOTE: A separate copy (i.e., the original assignment document or a true copy of the original document) must be submitted to Assignment Division in accordance with 37 CFR Part 3, if the assignment is to be recorded in the records of the PTO. See MPEP 302.08]

The undersigned (whose title is supplied below) is authorized to act on behalf of the assignee.

8-27-03

Date

RICHARD L. THURSTON

Typed or printed name



Signature

Vice President and General Counsel

Title

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.